ADVANCED MATERIALS AND DEVICES LABORATORIES
SCHOOL OF ENGINEERING, UNIVERSITY OF TOKYO

7-3-1 HONGO, BUNKYO-KU, TOKYO, 113, JAPAN

## SEMINAR ANNOUNCEMENT

**Denis Tregoat**
Alcatel Alsthom Corporate Research Center
Marcoussis, France

# "UV-250 PATTERNING OF SUB-MICRON TAPERED ACTIVE LAYERS"

**DATE: Tuesday, May 19, 1998**
**TIME: 11:00–11:30**
**PLACE: Rm. 400, Engineering Building 10**

### ABSTRACT

This paper reports the first results on Fabry-Perot 1.3 μm lasers with sub-micron tapered active layers defined using a UV-250 patterning technology in combination with conventional RIE processing of InP. Its implementation to the full 2 inch wafer process flow is of interest in low cost module fabrication. Short lasers (500 μm) with low coupling loss (3.4 dB with end cleaved fiber) and high quantum efficiency (0.26 W / A at 85°C) are demonstrated.

### BIOGRAPHY

Denis Tregoat was born in Lannion, France in December 1957. He received the Doctor degree from the University of Rennes (France) in 1985. In 1986, he joined Alcatel Alsthom Recherche, Marcoussis (France) where he was in charge of studies on fabrication processes for optical fibers (PCVD), and integrated optics (FHD). He is now working in the Optoelectronic Components Unit where he is involved in research activities on InP technology issues for high temperature 1.3 / 1.5μm laser, with emphasis on Reactive Ion Etching processes.

AMD Lab. Host: Yoshiaki Nakano

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